

Please amend the paragraph on page 11 from line 4 to line 22 as follows:

Embodiment 2:

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The configurations described in Embodiments 2, 3 and 4 are understood in relation to Figure 1 wherein the layers are sequenced from the top down, with second electrode 5 provided on carrier layer 6, made up of a base Si layer and a superimposed passivating layer of SiO<sub>2</sub>. To manufacture a filter arrangement with a bandpass filter and a notch filter, first the second electrode 5 comprising a thin Ti adhesion layer and a Pt layer was provided on a carrier layer or Si with a passivating layer of SiO<sub>2</sub>. A piezoelectric layer 4 of AlN was provided on this second electrode 5. Then a first electrode 3 comprising Pt was provided on the piezoelectric layer 4. The three layers were structured such that nine resonator units and one capacitor with a dielectric of AlN and the electrodes 3, 5 as well as an inductance were created. The lower electrode 3 was connected to ground. A 30nm thick, dense SiO<sub>2</sub> layer, thereon a porous SiO<sub>2</sub> layer in the form of an aerogel as a reflection element 2, and on this reflection element 2 a 300 nm thick layer of SiO<sub>2</sub> were deposited on the first electrode 3 in the region where the resonator units were present. A substrate 1 of glass was fastened on the entire assembly by means of acrylate glue. Then the Si layer of the carrier layer was etched away. Contact holes for contacting the first electrode 3 and the second electrode 5 were etched into the remaining SiO<sub>2</sub> layer. Subsequently, bump end contacts of Cr/Cu were grown in the contact holes.